CY62147CV25/30/33
MoBL™
256K x 16 Static RAM

Features

- **High Speed**
  - **55 ns and 70 ns availability**
- **Voltage range:**
  - **CY62147CV25: 2.2V–2.7V**
  - **CY62147CV30: 2.7V–3.3V**
  - **CY62147CV33: 3.0V–3.6V**
- **Pin Compatible with CY62147V**
- **Ultra-low active power**
  - **Typical active current: 1.5 mA @ f = 1 MHz**
  - **Typical active current: 5.5 mA @ f = f_{max} (70 ns speed)**
- **Low standby power**
- **Easy memory expansion with $\overline{CE}$ and $\overline{OE}$ features**
- **Automatic power-down when deselected**
- **CMOS for optimum speed/power**

Functional Description

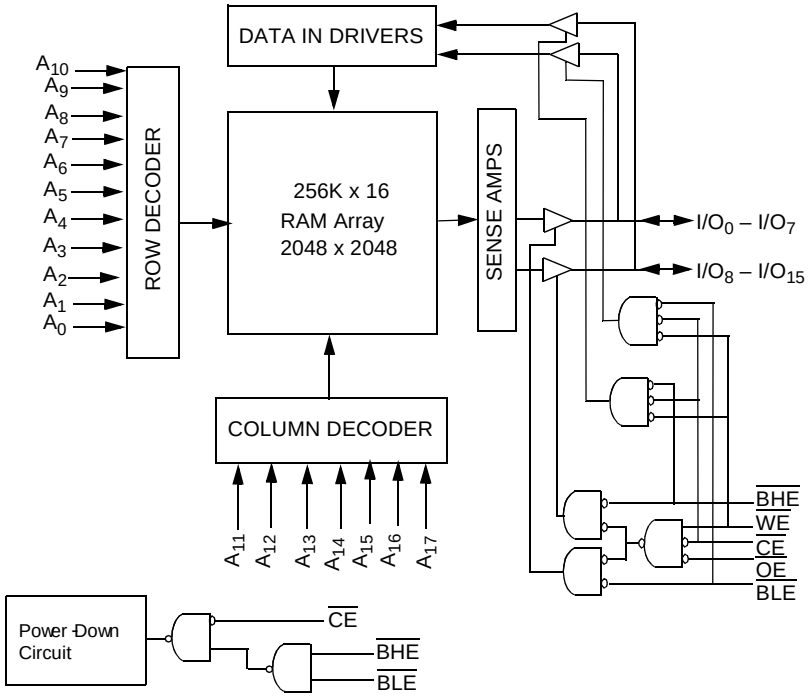
The CY62147CV25/30/33 are high-performance CMOS static RAMs organized as 256K words by 16 bits. These devices feature advanced circuit design to provide ultra-low active current. This is ideal for providing More Battery Life™ (MoBL™) in portable applications such as cellular telephones. The devices also have an automatic power-down feature that significantly reduces power consumption by 80% when addresses are not toggling. The device can also be put into standby mode reducing power consumption by more than 99% when deselected ($\overline{CE}$ HIGH or both $\overline{BLE}$ and $\overline{BHE}$ are HIGH). The input/output pins (I/O_0 through I/O_{15}) are placed in a high-impedance state when: deselected ($\overline{CE}$ HIGH), outputs are disabled ($\overline{OE}$ HIGH), both Byte High Enable and Byte Low Enable are disabled ($\overline{BHE}$, $\overline{BLE}$ HIGH), or during a write operation ($\overline{CE}$ LOW and $\overline{WE}$ LOW).

Writing to the device is accomplished by taking Chip Enable ($\overline{CE}$) and Write Enable ($\overline{WE}$) inputs LOW. If Byte Low Enable ($\overline{BLE}$) is LOW, then data from I/O pins (I/O_0 through I/O_7), is written into the location specified on the address pins (A_0 through A_{17}). If Byte High Enable ($\overline{BHE}$) is LOW, then data from I/O pins (I/O_8 through I/O_{15}) is written into the location specified on the address pins (A_0 through A_{17}).

Reading from the device is accomplished by taking Chip Enable ($\overline{CE}$) and Output Enable ($\overline{OE}$) LOW while forcing the Write Enable ($\overline{WE}$) HIGH. If Byte Low Enable ($\overline{BLE}$) is LOW, then data from the memory location specified by the address pins will appear on I/O_0 to I/O_7. If Byte High Enable ($\overline{BHE}$) is LOW, then data from memory will appear on I/O_8 to I/O_{15}. See the truth table at the back of this data sheet for a complete description of read and write modes.

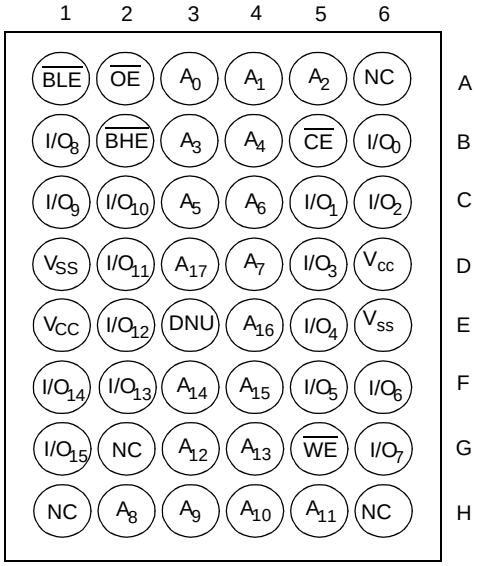
The CY62147CV25/30/33 are available in a 48-ball FBGA package.

Logic Block Diagram



Pin Configuration[1, 2]

FBGA (Top View)



Maximum Ratings

(Above which the useful life may be impaired. For user guidelines, not tested.)

Storage Temperature ..... –65°C to +150°C

Ambient Temperature with Power Applied..... –55°C to +125°C

Supply Voltage to Ground Potential... –0.5V to V_{ccmax} + 0.5V

DC Voltage Applied to Outputs in High Z State[3]..... –0.5V to V_{CC} + 0.3V

DC Input Voltage[3] ..... -0.5V to V_{CC} + 0.3V

Output Current into Outputs (LOW) ..... 20 mA

Static Discharge Voltage ..... >2001V (per MIL-STD-883, Method 3015)

Latch-Up Current..... >200 mA

Operating Range

Device	Range	Ambient Temperature	V_{CC}
CY62147CV25	Industrial	–40°C to +85°C	2.2V to 2.7V
CY62147CV30			2.7V to 3.3V
CY62147CV33			3.0V to 3.6V

Product Portfolio

Product	V_{CC} Range			Speed	Power Dissipation (Industrial)					
					Operating, I_{CC}				Standby (I_{SB2})	
					f = 1 MHz		f = f_{max}			
	$V_{CC(min.)}$	$V_{CC(typ.)}$[4]	$V_{CC(max.)}$		Typ.[4]	Max.	Typ.[4]	Max.	Typ.[4]	Max.
CY62147CV25	2.2V	2.5V	2.7V	55 ns	1.5 mA	3 mA	7 mA	15 mA	5 µA	15 µA
				70 ns	1.5 mA	3 mA	5.5 mA	12 mA		
CY62147CV30	2.7V	3.0V	3.3V	55 ns	1.5 mA	3 mA	7 mA	15 mA	7 µA	15 µA
				70 ns	1.5 mA	3 mA	5.5 mA	12 mA		
CY62147CV33	3.0V	3.3V	3.6V	55 ns	1.5 mA	3 mA	7 mA	15 mA	8 µA	20 µA
				70 ns	1.5 mA	3 mA	5.5 mA	12 mA		

Notes:
1. NC pins are not connected to the die.
2. E3 (DNU) can be left as NC or V_{SS} to ensure proper application.
3. $V_{IL(min.)}$ = –2.0V for pulse durations less than 20 ns.
4. Typical values are included for reference only and are not guaranteed or tested. Typical values are measured at V_{CC} = $V_{CC(typ.)}$, T_A = 25°C.

Electrical Characteristics Over the Operating Range

Parameter	Description	Test Conditions		CY62147CV25-55 Min.	CY62147CV25-55 Typ.[4]	CY62147CV25-55 Max.	CY62147CV25-70 Min.	CY62147CV25-70 Typ.[4]	CY62147CV25-70 Max.	Unit
V_{OH}	Output HIGH Voltage	I_{OH} = –0.1 mA	V_{CC} = 2.2V	2.0			2.0			V
V_{OL}	Output LOW Voltage	I_{OL} = 0.1 mA	V_{CC} = 2.2V			0.4			0.4	V
V_{IH}	Input HIGH Voltage			1.8		V_{CC} + 0.3V	1.8		V_{CC} + 0.3V	V
V_{IL}	Input LOW Voltage			–0.3		0.6	–0.3		0.6	V
I_{IX}	Input Leakage Current	GND ≤ V_I ≤ V_{CC}		–1		+1	–1		+1	µA
I_{OZ}	Output Leakage Current	GND ≤ V_O ≤ V_{CC}, Output Disabled		–1		+1	–1		+1	µA
I_{CC}	V_{CC} Operating Supply Current	f = f_{MAX} = $1/t_{RC}$	V_{CC} = 2.7V, I_{OUT} = 0 mA CMOS Levels		7	15		5.5	12	mA
		f = 1 MHz			1.5	3		1.5	3	
I_{SB1}	Automatic CE Power-Down Current— CMOS Inputs	$\overline{CE}$ ≥ V_{CC} – 0.2V, V_{IN} ≥ V_{CC} – 0.2V or V_{IN} ≤ 0.2V, f = f_{max} (Address and Data Only), f=0 ($\overline{OE}$,$\overline{WE}$,$\overline{BHE}$ and $\overline{BLE}$)			5	15		5	15	µA
I_{SB2}	Automatic CE Power-Down Current— CMOS Inputs	$\overline{CE}$ ≥ V_{CC} – 0.2V, V_{IN} ≥ V_{CC} – 0.2V or V_{IN} ≤ 0.2V, f = 0, V_{CC} = 2.7V								

Parameter	Description	Test Conditions		CY62147CV30-55 Min.	CY62147CV30-55 Typ.[4]	CY62147CV30-55 Max.	CY62147CV30-70 Min.	CY62147CV30-70 Typ.[4]	CY62147CV30-70 Max.	Unit
V_{OH}	Output HIGH Voltage	I_{OH} = –1.0 mA	V_{CC} = 2.7V	2.4			2.4			V
V_{OL}	Output LOW Voltage	I_{OL} = 2.1 mA	V_{CC} = 2.7V			0.4			0.4	V
V_{IH}	Input HIGH Voltage			2.2		V_{CC} + 0.3V	2.2		V_{CC} + 0.3V	V
V_{IL}	Input LOW Voltage			–0.3		0.8	–0.3		0.8	V
I_{IX}	Input Leakage Current	GND ≤ V_I ≤ V_{CC}		–1		+1	–1		+1	µA
I_{OZ}	Output Leakage Current	GND ≤ V_O ≤ V_{CC}, Output Disabled		–1		+1	–1		+1	µA
I_{CC}	V_{CC} Operating Supply Current	f = f_{MAX} = $1/t_{RC}$	V_{CC} = 3.3V, I_{OUT} = 0 mA CMOS Levels		7	15		5.5	12	mA
		f = 1 MHz			1.5	3		1.5	3	
I_{SB1}	Automatic CE Power-Down Current— CMOS Inputs	$\overline{CE}$ ≥ V_{CC} – 0.2V, V_{IN} ≥ V_{CC} – 0.2V or V_{IN} ≤ 0.2V, f = f_{max} (Address and Data Only), f=0 ($\overline{OE}$,$\overline{WE}$,$\overline{BHE}$ and $\overline{BLE}$)			7	15		7	15	µA
I_{SB2}	Automatic CE Power-Down Current— CMOS Inputs	$\overline{CE}$ ≥ V_{CC} – 0.2V, V_{IN} ≥ V_{CC} – 0.2V or V_{IN} ≤ 0.2V, f = 0, V_{CC} = 3.3V								

Electrical Characteristics Over the Operating Range (continued)

Parameter	Description	Test Conditions		CY62147CV33-55			CY62147CV33-70			Unit
				Min.	Typ.[4]	Max.	Min.	Typ.[4]	Max.	
V_{OH}	Output HIGH Voltage	I_{OH} = –1.0 mA	V_{CC} = 3.0V	2.4			2.4			V
V_{OL}	Output LOW Voltage	I_{OL} = 2.1 mA	V_{CC} = 3.0V			0.4			0.4	V
V_{IH}	Input HIGH Voltage			2.2		V_{CC} + 0.3V	2.2		V_{CC} + 0.3V	V
V_{IL}	Input LOW Voltage			–0.3		0.8	–0.3		0.8	V
I_{IX}	Input Leakage Current	GND ≤ V_I ≤ V_{CC}		–1		+1	–1		+1	µA
I_{OZ}	Output Leakage Current	GND ≤ V_O ≤ V_{CC}, Output Disabled		–1		+1	–1		+1	µA
I_{CC}	V_{CC} Operating Supply Current	f = f_{MAX} = 1/t_{RC}	V_{CC} = 3.6V I_{OUT} = 0 mA CMOS Levels		7	15		5.5	12	mA
		f = 1 MHz			1.5	3		1.5	3	
I_{SB1}	Automatic CE Power-Down Current— CMOS Inputs	$\overline{CE}$ ≥ V_{CC} – 0.2V V_{IN} ≥ V_{CC} – 0.2V or V_{IN} ≤ 0.2V, f = f_{max} (Address and Data Only), f=0 (OE,WE,BHE and BLE)			8	20		8	20	µA
I_{SB2}	Automatic CE Power-Down Current— CMOS Inputs	$\overline{CE}$ ≥ V_{CC} – 0.2V V_{IN} ≥ V_{CC} – 0.2V or V_{IN} ≤ 0.2V, f = 0, V_{CC} = 3.6V								

Capacitance[5]

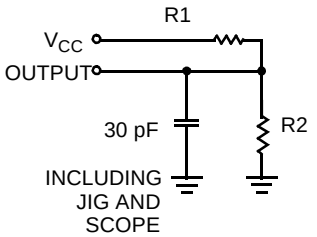
Parameter	Description	Test Conditions	Max.	Unit
C_{IN}	Input Capacitance	T_A = 25°C, f = 1 MHz, V_{CC} = $V_{CC(typ.)}$	6	pF
C_{OUT}	Output Capacitance		8	pF

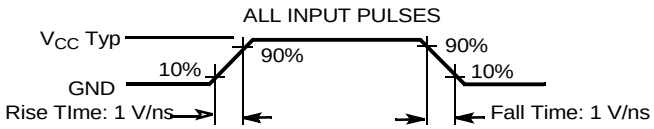
Thermal Resistance

Description	Test Conditions	Symbol	BGA	Unit
Thermal Resistance (Junction to Ambient)[5]	Still Air, soldered on a 3 x 4.5 inch, two-layer printed circuit board	Θ_{JA}	55	°C/W
Thermal Resistance (Junction to Case)[5]		Θ_{JC}	16	°C/W

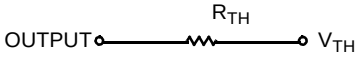
Note:
5. Tested initially and after any design or process changes that may affect these parameters.

AC Test Loads and Waveforms





Equivalent to: THÉVENIN EQUIVALENT

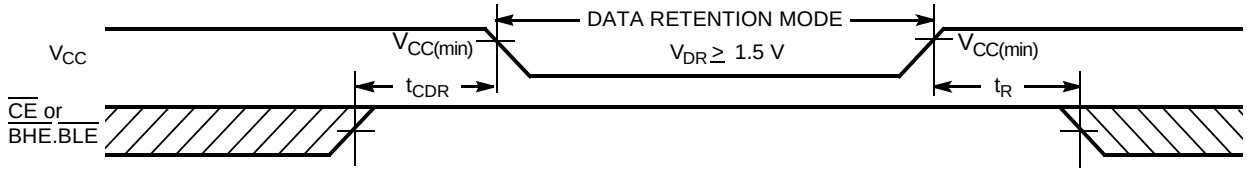


Parameters	2.5V	3.0V	3.3V	Unit
R1	16.6	1.105	1.216	KΩ
R2	15.4	1.550	1.374	KΩ
R_{TH}	8	0.645	0.645	KΩ
V_{TH}	1.20	1.75	1.75	Volts

Data Retention Characteristics (Over the Operating Range)

Parameter	Description	Conditions	Min.	Typ.[4]	Max.	Unit
V_{DR}	V_{CC} for Data Retention		1.5		V_{ccmax}	V
I_{CCDR}	Data Retention Current	V_{CC}= 1.5V $\overline{CE} \geq V_{CC} - 0.2V$, $V_{IN} \geq V_{CC} - 0.2V$ or $V_{IN} \leq 0.2V$		3	10	µA
t_{CDR}[5]	Chip Deselect to Data Retention Time		0			ns
t_R[6]	Operation Recovery Time		t_{RC}			ns

Data Retention Waveform[7]



Note:
6. Full Device AC operation requires linear V_{CC} ramp from V_{DR} to $V_{CC(min.)}$ > 100µs or stable at $V_{CC(min.)}$ >100 µs.
7. $\overline{BHE}.\overline{BLE}$ is the AND of both $\overline{BHE}$ and $\overline{BLE}$. Chip can be deselected by either disabling the chip enable signals or by disabling both $\overline{BHE}$ and $\overline{BLE}$.

Switching Characteristics Over the Operating Range[8]

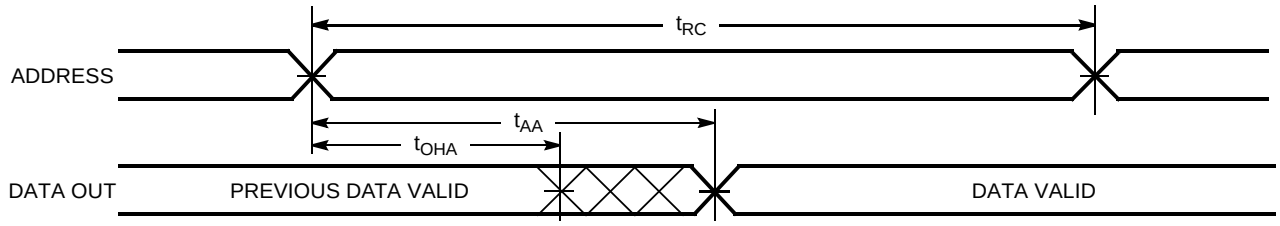
Parameter	Description	55 ns		70 ns		Unit
		Min	Max	Min	Max	
READ CYCLE						
t_{RC}	Read Cycle Time	55		70		ns
t_{AA}	Address to Data Valid		55		70	ns
t_{OHA}	Data Hold from Address Change	10		10		ns
t_{ACE}	$\overline{CE}$ LOW to Data Valid		55		70	ns
t_{DOE}	$\overline{OE}$ LOW to Data Valid		25		35	ns
t_{LZOE}	$\overline{OE}$ LOW to Low Z[9]	5		5		ns
t_{HZOE}	$\overline{OE}$ HIGH to High Z[9, 11]		20		25	ns
t_{LZCE}	$\overline{CE}$ LOW to Low Z[9]	10		10		ns
t_{HZCE}	$\overline{CE}$ HIGH to High Z[9, 11]		20		25	ns
t_{PU}	$\overline{CE}$ LOW to Power-Up	0		0		ns
t_{PD}	$\overline{CE}$ HIGH to Power-Down		55		70	ns
t_{DBE}	$\overline{BHE}$ / $\overline{BLE}$ LOW to Data Valid		55		70	ns
t_{LZBE}[10]	$\overline{BHE}$ / $\overline{BLE}$ LOW to Low Z[9]	5		5		ns
t_{HZBE}	$\overline{BHE}$ / $\overline{BLE}$ HIGH to High Z[9, 11]		20		25	ns
WRITE CYCLE[12]						
t_{WC}	Write Cycle Time	55		70		ns
t_{SCE}	$\overline{CE}$ LOW to Write End	45		60		ns
t_{AW}	Address Set-Up to Write End	45		60		ns
t_{HA}	Address Hold from Write End	0		0		ns
t_{SA}	Address Set-Up to Write Start	0		0		ns
t_{PWE}	$\overline{WE}$ Pulse Width	45		50		ns
t_{BW}	$\overline{BHE}$ / $\overline{BLE}$ Pulse Width	50		60		ns
t_{SD}	Data Set-Up to Write End	25		30		ns
t_{HD}	Data Hold from Write End	0		0		ns
t_{HZWE}	$\overline{WE}$ LOW to High Z[9, 11]		20		25	ns
t_{LZWE}	$\overline{WE}$ HIGH to Low Z[9]	5		5		ns

Notes:

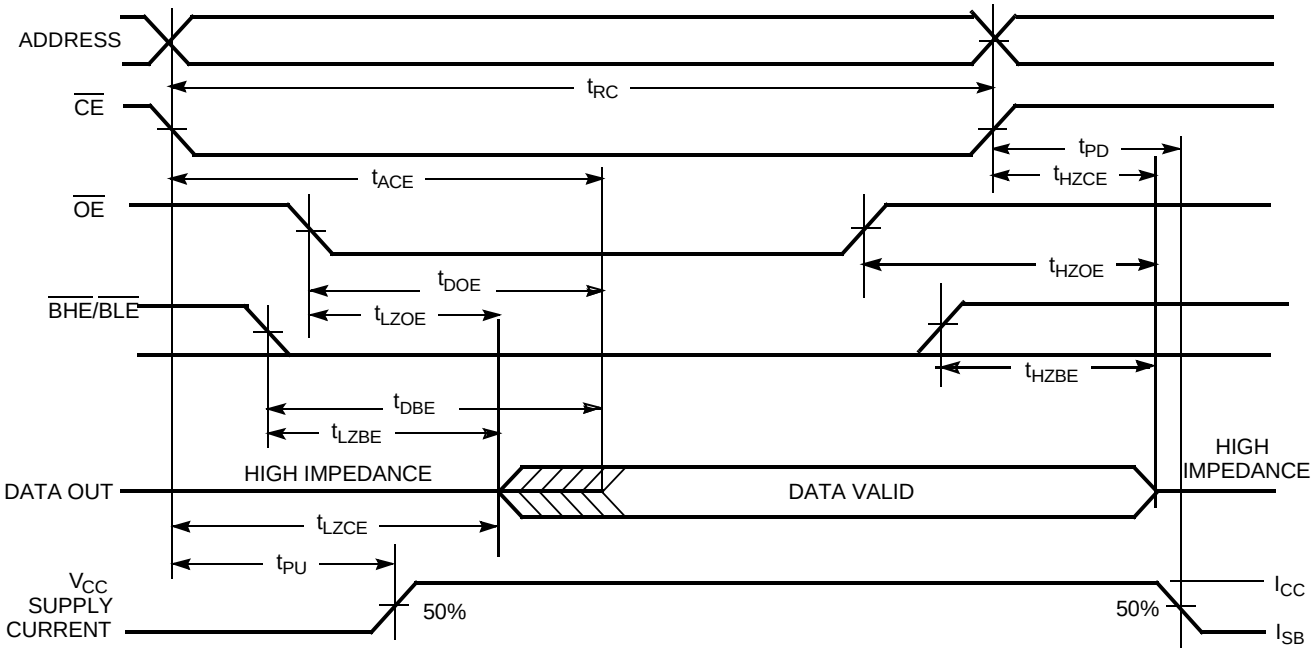
8. Test conditions assume signal transition time of 5 ns or less, timing reference levels of $V_{CC(typ.)}/2$, input pulse levels of 0 to $V_{CC(typ.)}$, and output loading of the specified I_{OL}/I_{OH} and 30-pF load capacitance.
9. At any given temperature and voltage condition, t_{HZCE} is less than t_{LZCE}, t_{HZBE} is less than t_{LZBE}, t_{HZOE} is less than t_{LZOE}, and t_{HZWE} is less than t_{LZWE} for any given device.
10. If both byte enables are toggled together this value is 10 ns.
11. t_{HZOE}, t_{HZCE}, t_{HZBE}, and t_{HZWE} transitions are measured when the outputs enter a high impedance state.
12. The internal write time of the memory is defined by the overlap of $\overline{WE}$, $\overline{CE}$ = V_{IL}, $\overline{BHE}$ and/or $\overline{BLE}$ = V_{IL}. All signals must be ACTIVE to initiate a write and any of these signals can terminate a write by going INACTIVE. The data input set-up and hold timing should be referenced to the edge of the signal that terminates the write.

Switching Waveforms

Read Cycle No. 1 (Address Transition Controlled) [13, 14]



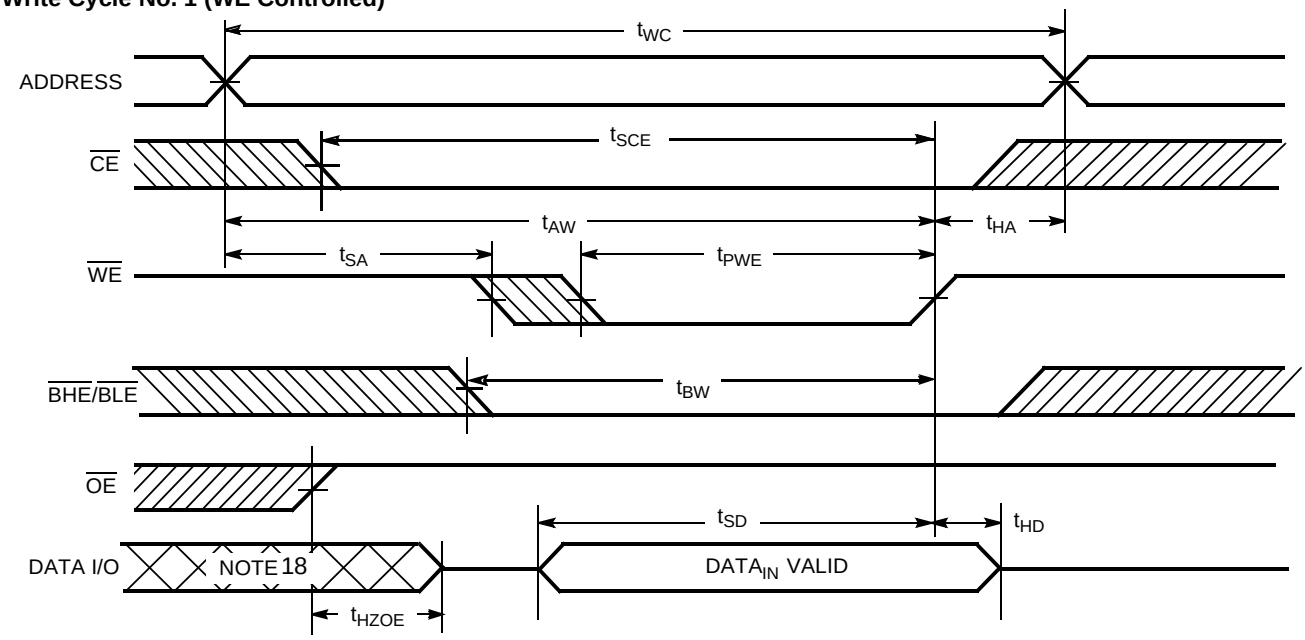
Read Cycle No. 2 (OE Controlled) [14, 15]



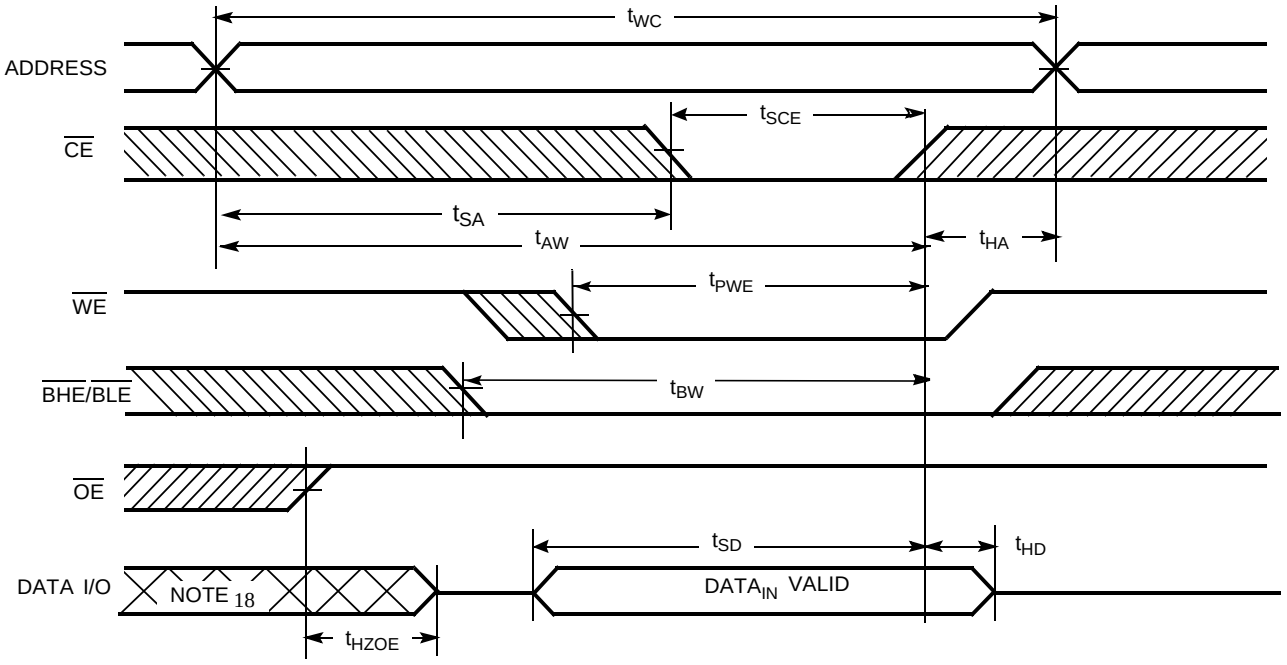
Notes:
13. Device is continuously selected. OE, CE = V_{IL}, BHE and/or BLE = V_{IL}.
14. WE is HIGH for read cycle.
15. Address valid prior to or coincident with CE, BHE, BLE transition LOW.

Switching Waveforms (continued)

Write Cycle No. 1 ($\overline{WE}$ Controlled) [12, 16, 17]



Write Cycle No. 2 ($\overline{CE}$ Controlled) [12, 16, 17]

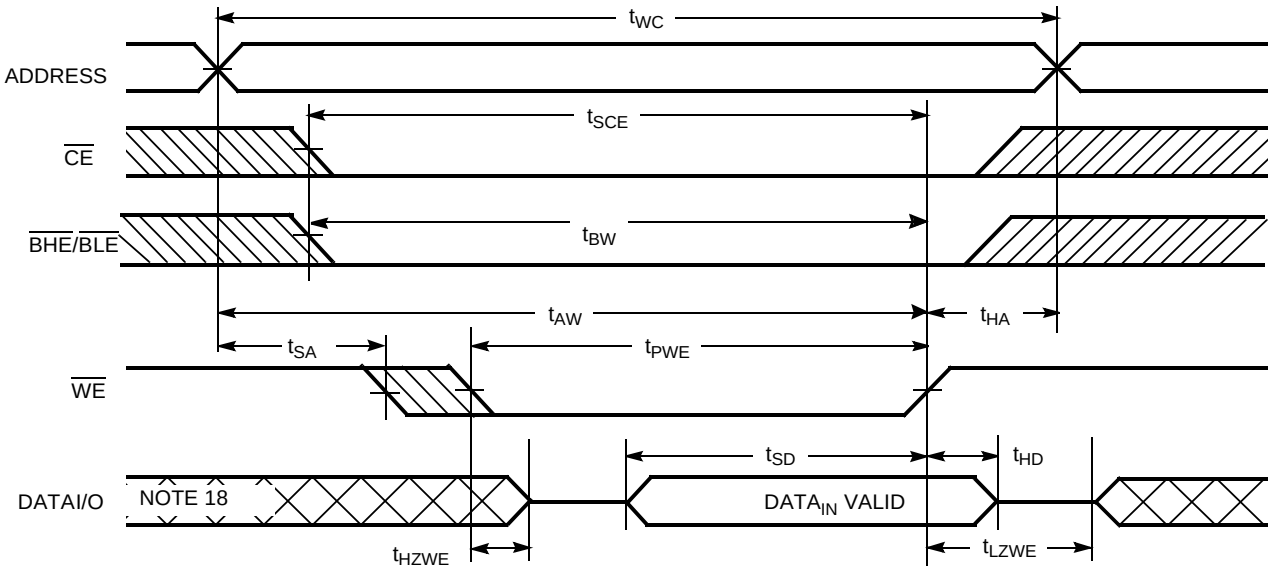


Notes:

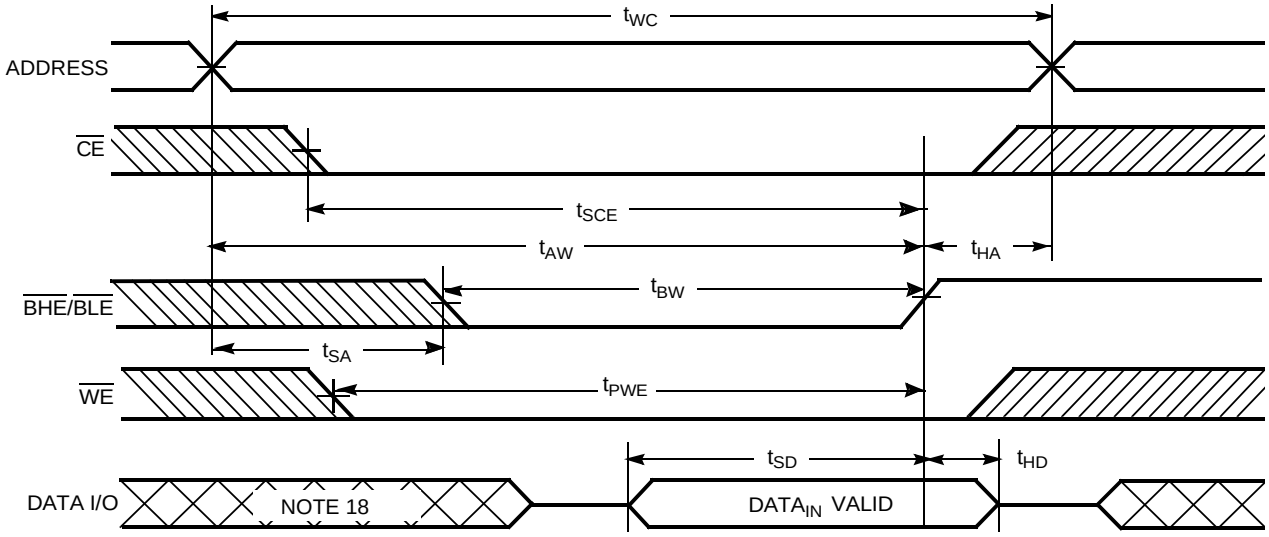
16. Data I/O is high-impedance if $\overline{OE} = V_{IH}$.
17. If $\overline{CE}$ goes HIGH simultaneously with $\overline{WE}$ HIGH, the output remains in a high-impedance state.
18. During this period, the I/Os are in output state and input signals should not be applied.

Switching Waveforms (continued)

Write Cycle No. 3 (WE Controlled, OE LOW) [17]



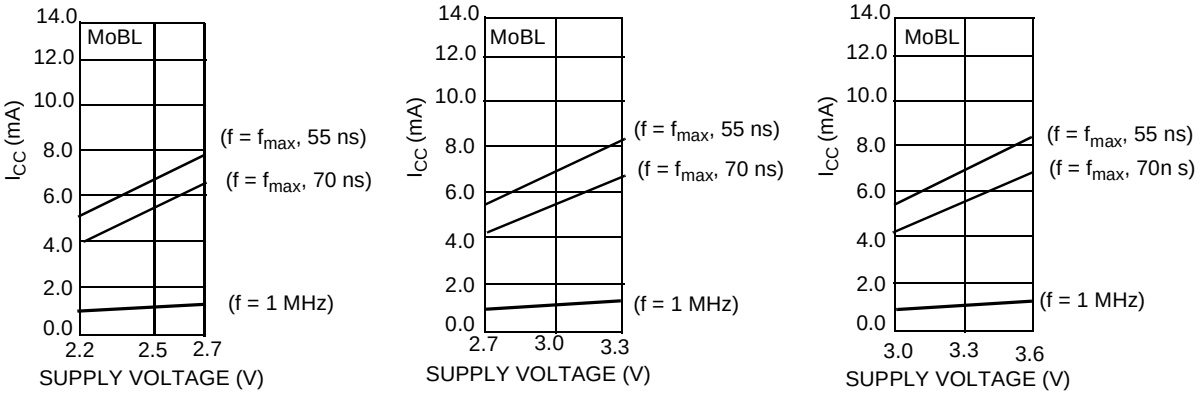
Write Cycle No. 4 (BHE/BLE Controlled, OE LOW) [17]



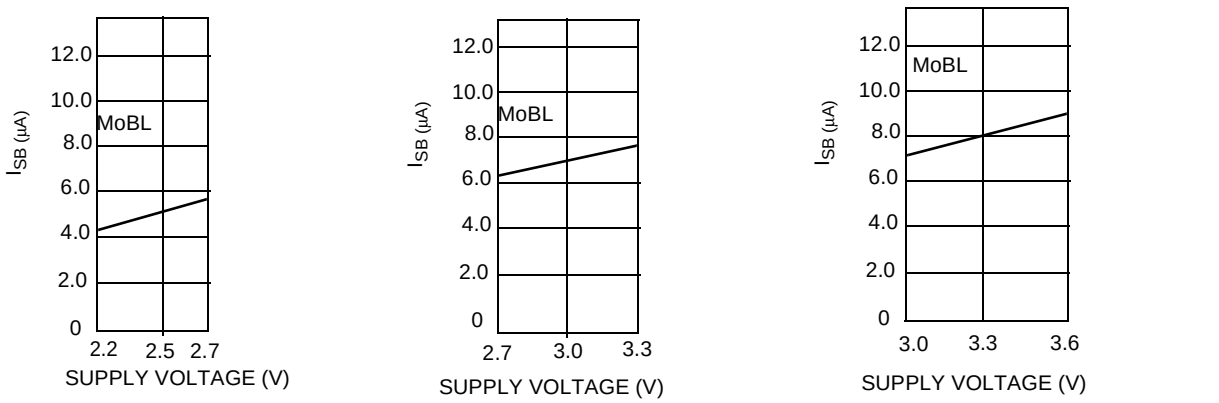
Typical DC and AC Parameters

(Typical values are included for reference only and are not guaranteed or tested. Typical values are measured at $V_{CC} = V_{CC(typ.)}$, $T_A = 25°C$.)

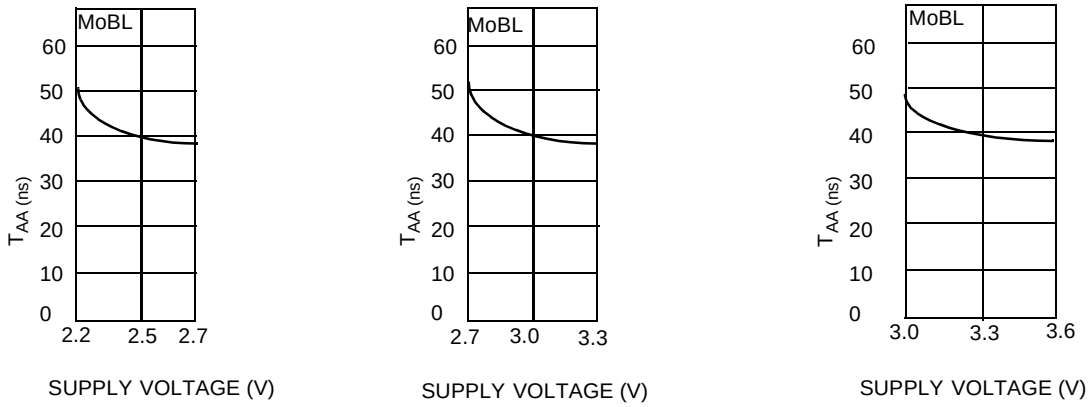
Operating Current vs. Supply Voltage



Standby Current vs. Supply Voltage



Access Time vs. Supply Voltage



Truth Table

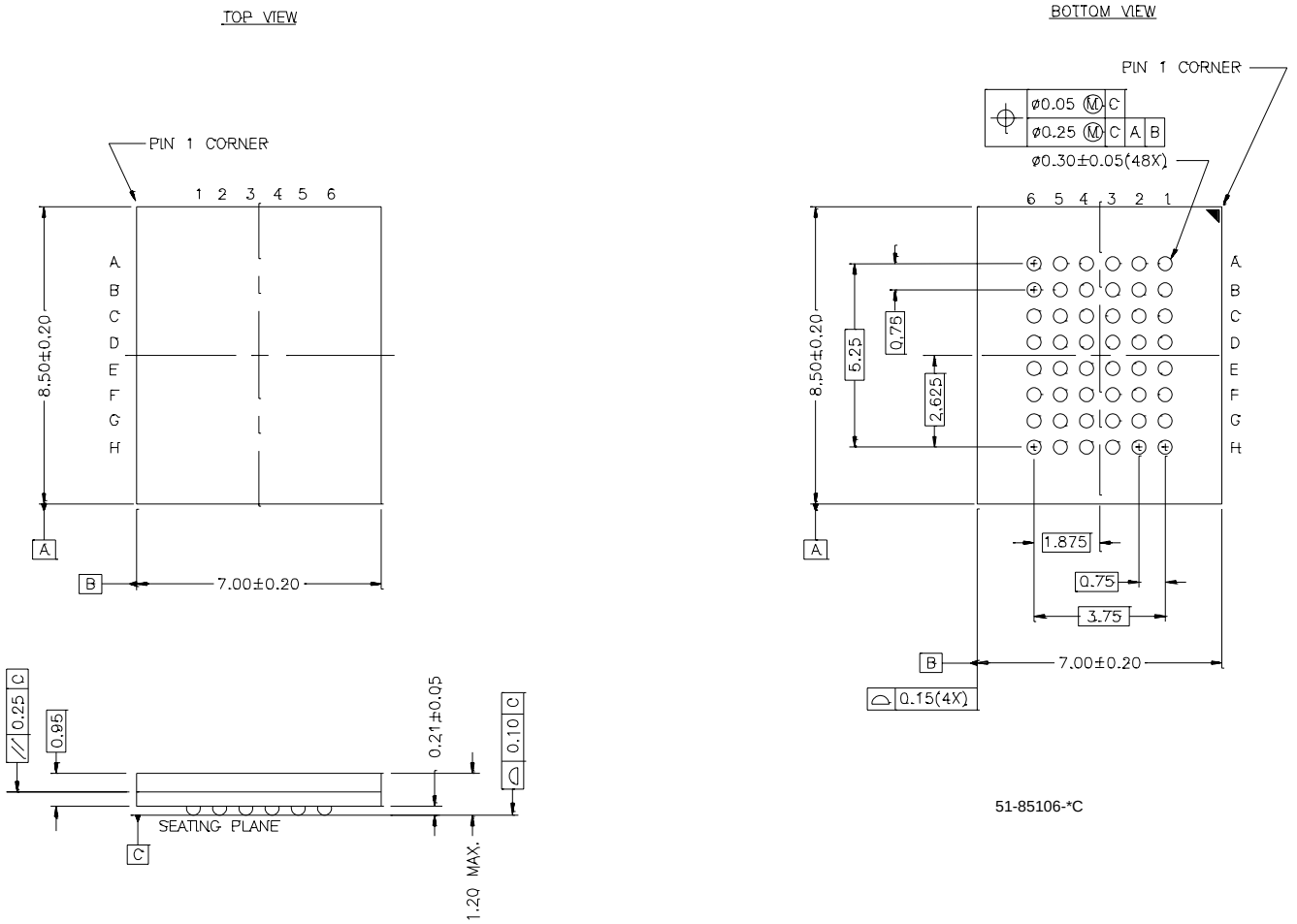
$\overline{CE}$	$\overline{WE}$	$\overline{OE}$	$\overline{BHE}$	$\overline{BLE}$	Inputs/Outputs	Mode	Power
H	X	X	X	X	High Z	Deselect/Power-Down	Standby (I_{SB})
X	X	X	H	H	High Z	Deselect/Power-Down	Standby (I_{SB})
L	H	L	L	L	Data Out (I/O_O–I/O_{15})	Read	Active (I_{CC})
L	H	L	H	L	Data Out (I/O_O–I/O_7); I/O_8–I/O_{15} in High Z	Read	Active (I_{CC})
L	H	L	L	H	Data Out (I/O_8–I/O_{15}); I/O_0–I/O_7 in High Z	Read	Active (I_{CC})
L	H	H	L	L	High Z	Output Disabled	Active (I_{CC})
L	H	H	H	L	High Z	Output Disabled	Active (I_{CC})
L	H	H	L	H	High Z	Output Disabled	Active (I_{CC})
L	L	X	L	L	Data In (I/O_O–I/O_{15})	Write	Active (I_{CC})
L	L	X	H	L	Data In (I/O_O–I/O_7); I/O_8–I/O_{15} in High Z	Write	Active (I_{CC})
L	L	X	L	H	Data In (I/O_8–I/O_{15}); I/O_0–I/O_7 in High Z	Write	Active (I_{CC})

Ordering Information

Speed (ns)	Ordering Code	Package Name	Package Type	Operating Range
70	CY62147CV25LL-70BAI	BA48B	48-Ball Fine Pitch BGA (7 mm x 8.5 mm x 1.2 mm)	Industrial
	CY62147CV25LL-70BVI	BV48A	48-Ball Fine Pitch BGA (6 mm x 8 mm x 1 mm)	
	CY62147CV30LL-70BAI	BA48B	48-Ball Fine Pitch BGA (7 mm x 8.5 mm x 1.2 mm)	
	CY62147CV30LL-70BVI	BV48A	48-Ball Fine Pitch BGA (6 mm x 8 mm x 1 mm)	
	CY62147CV33LL-70BAI	BA48B	48-Ball Fine Pitch BGA (7 mm x 8.5 mm x 1.2 mm)	
	CY62147CV33LL-70BVI	BV48A	48-Ball Fine Pitch BGA (6 mm x 8 mm x 1 mm)	
55	CY62147CV25LL-55BAI	BA48B	48-Ball Fine Pitch BGA (7 mm x 8.5 mm x 1.2 mm)	
	CY62147CV25LL-55BVI	BV48A	48-Ball Fine Pitch BGA (6 mm x 8 mm x 1 mm)	
	CY62147CV30LL-55BAI	BA48B	48-Ball Fine Pitch BGA (7 mm x 8.5 mm x 1.2 mm)	
	CY62147CV30LL-55BVI	BV48A	48-Ball Fine Pitch BGA (6 mm x 8 mm x 1 mm)	
	CY62147CV33LL-55BAI	BA48B	48-Ball Fine Pitch BGA (7 mm x 8.5 mm x 1.2 mm)	
	CY62147CV33LL-55BVI	BV48A	48-Ball Fine Pitch BGA (6 mm x 8 mm x 1 mm)	

Package Diagrams

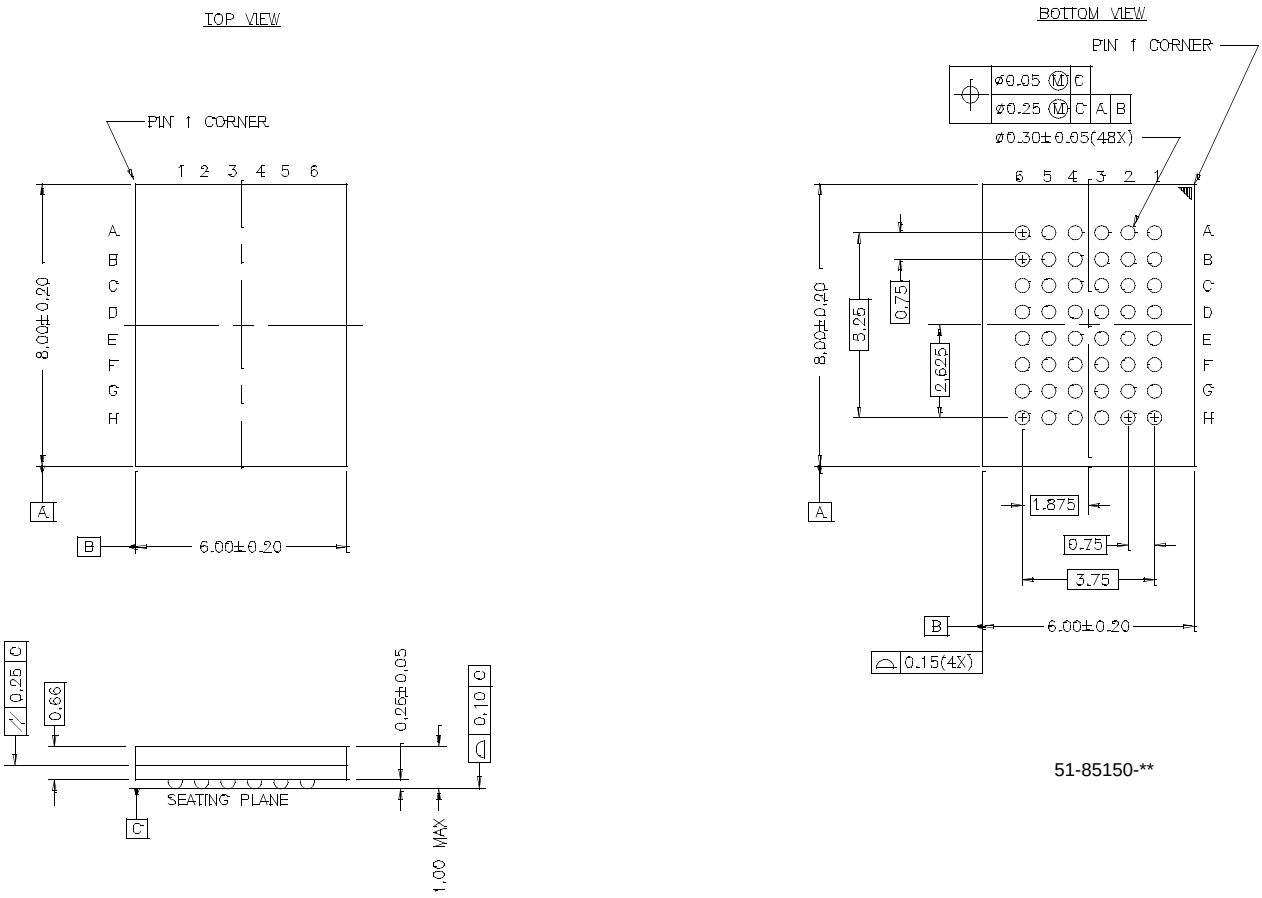
48-Ball (7.00 mm x 8.5 mm x 1.2 mm) Thin BGA BA48B



51-85106-*C

Package Diagrams (continued)

48-Lead VFBGA (6 mm x 8 mm x 1 mm) BV48A



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REV.	**ECN NO.**	**Issue Date**	**Orig. of Change**	**Description of Change**
**	112394	01/31/02	GAV	Converted from Spec# 38-01123 to 38-05202. Advance Information to Final
*A	114216	05/01/02	MGN/GUG	Improved Typical & Max Icc values